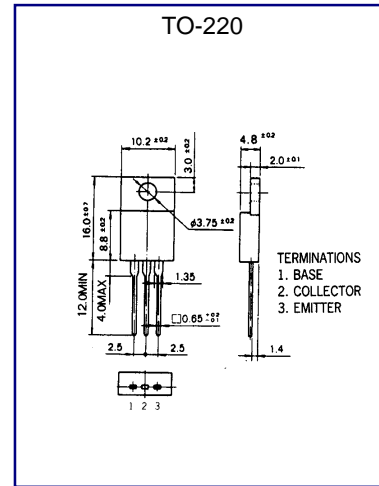




**BU406D**

**NPN EPITAXIAL SILICON TRANSISTOR**

**HIGH VOLTAGE SWITCHING USE IN  
HORIZONTAL DEFLECTION OUTPUT STAGE**



**ABSOLUTE MAXIMUM RATINGS (Ta=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	400	V
Collector-Emitter Voltage	VCEO	400	V
Emitter-Base voltage	VEBO	6	V
Collector Current (DC)	IC	7	A
Collector Peak Current	ICM	10	A
Base Current (DC)	IB	4	A
Collector Dissipation (Tc=25°C)	PC	60	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65~150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current (VBE=0)	ICES	VCE= 400V, VEB= 0			5	mA
Emitter Cutoff Current(IC=0)	IEBO	VEB= 6V, IC=0			1	mA
Collector Emitter Saturation Voltage	VCE(sat)	IC=5A, IB=0.5A			1.2	V
Base- Emitter Saturation Voltage	VBE(sat)	IC=5A, IB=1.2A			1.5	V
Current Gain Bandwidth Product	fT	VCE= 10V, IC=500mA	10			MHZ
Turn-Off Time	toff	IC=5A, IB=0.5A			0.75	µS
		IC=5A, IB=0.8A			0.4	µS
		IC=6A, IB=1.2A			0.4	µS